

FOR USE BY ELECTRICIANS OVERSEAS:

最新トランジスタ規格表 (New Transistor Manual) lists all the transistors registered with the Electronic Industries Association of Japan (EIAJ), arranged in a manner easy to look up. We hope that you will make full use of the data provided in this manual by referring to the Japanese-English translation key given below.

型名	社名	用途	構造	最大定格 ($T_a=25^{\circ}\text{C}$)					電 気 的 特 性 ($T_a=25^{\circ}\text{C}$)										外形	備考
				V_{ceo} (V)	V_{cso} (V)	I_c (mA)	P_c (mW)	T_j ($^{\circ}\text{C}$)	I_{cso} 最大値 (μA)	$V_{ce(V)}$	直流又はパルス h_{FE} I_c (mA)	バイアス $V_{ce(V)}$	h_{FE} h_{FE}^*	h_{ie} h_{ie}^* (Ω)	h_{re} h_{re}^* ($\times 10^{-4}$)	h_{oe} h_{oe}^* (μS)	$f_{\alpha b}$ $f_{\alpha b}^*$ (Mc)	C_{ob} (pF)	$r_{bb'}$ $r_{bb'}^*$ (Ω)	
1	2	3	4	5					6	7		8			9			10	11	12

- 1 TYPE NUMBER
- 2 ORIGINAL MANUFACTURER
- 3 USES
- 4 MATERIAL AND STRUCTURE
- 5 MAXIMUM RATINGS
- 6 I_{cso} MAXIMUM VALUE AND V_{ce} VALUE (CRITERIA FOR MEASURING I_{cso})
- 7 STANDARD VALUE OF DC/PULSE h_{FE} AND V_{ce} , I_c (CRITERIA FOR MEASURING DC/PULSE h_{FE})
- 8 STANDARD VALUE OF h PARAMETERS AND BIAS V_{ce} , I_E (CRITERIA FOR MEASURING h PARAMETERS)

* INDICATES VALUE IN GROUNDED-BASE OPERATION, OTHERWISE VALUE IN EMITTER-GROUNDED OPERATION.

- 9 $f_{\alpha b}$ OF RF CHARACTERISTIC, EXCEPT IN CASE OF * WHICH INDICATES VALUE OF f_T .
- 10 C_{ob} AND $r_{bb'}$ OF RF CHARACTERISTICS EXCEPT IN CASE OF * IN $r_{bb'}$ COLUMN WHICH INDICATES VALUE OF h_{ie} (real)
- 11 OUTLINE
- 12 REMARKS

: とコンプリ: COMPLEMENTARY TO

型 名	社 名	用 途	構 造	最大 定 格 (T _a = 25℃)					電 気 的 特 性 (T _a = 25℃)											外 形	備 考				
				V _{CEO} (V)	V _{EB0} (V)	I _C (mA)	P _C (mW)	T _j (℃)	I _{CHO} 最大値		直 流 又 は パ ル ス hFE					バ イ ア ス									
									μA	V _{CE(V)}	V _{CE} (V)	I _C (mA)	V _{CE(V)}	I _E (mA)	h _{FE}	h _{FE} *	h _{FE} *	h _{FE} *	f _{os} fT*			C _{ob} (pF)	r _{bb} h _{FE} (real)*		
				(V)	(V)	(mA)	(mW)	(℃)	(μA)	V _{CE(V)}	V _{CE} (V)	I _C (mA)	V _{CE(V)}	I _E (mA)	h _{FE} *	h _{FE} *	h _{FE} *	h _{FE} *	f _{os} fT*	C _{ob} (pF)	r _{bb} h _{FE} (real)*				
2SC2622																									
" 2623	富士電機	SW. PA	Si. TP	450	7	20A	100W (T _a =25℃)	150	1 mA	450	20	5	8 A			t _{on} < 1 μS, t _{off} < 3 μS							102		
" 2624	"	SW	"	450	7	5 A	80W (T _a =25℃)	150	1 mA	450	>10	5	2 A			t _{on} < 1 μS, t _{off} < 2 μS							220		
" 2625	"	"	"	450	7	10A	80W (T _a =25℃)	150	1 mA	450	>10	5	4 A			t _{on} < 1 μS, t _{off} < 2 μS							220		
" 2626	"	"	"	400	7	15A	80W (T _a =25℃)	150	1 mA	400	>10	5	6 A			t _{on} < 0.8 μS, t _{off} < 2 μS							220		
" 2627	三 菱	RF. PA	Si. EP	35	4	2 A	20W (T _a =25℃)	175	1 mA	25	80	10	100			P _a = 6 W, η = 70% (f = 175MHz, V _{CE} = 12.5V, P _i = 0.25W)							187		
" 2628	"	"	"	35	4	4 A	40W (T _a =25℃)	175	2 mA	25	30	10	100			P _a = 18W, η = 70% (f = 175MHz, V _{CE} = 12.5V, P _i = 1 W)							187		
" 2629	"	"	"	35	4	8 A	60W (T _a =25℃)	175	3 mA	25	40	10	200			P _a = 34W, η = 70% (f = 175MHz, V _{CE} = 12.5V, P _i = 3.5W)							187		
" 2630	"	"	"	35	4	14A	100W (T _a =25℃)	175	5 mA	25	40	10	200			P _a = 60W, η = 70% (f = 175MHz, V _{CE} = 12.5V, P _i = 10W)							303	各リード 端子間の 絶縁	
" 2631	松 下	AF		150	5	50	750	150	1	100	65~450	5	10	10	-10	V _{CEO} = 150mV (10V, 1mA, R _{CE} = 100kΩ, G _{CE} = 80dB)	160 *	2					138	2SA1123 とコンプリ	
" 2632	"	"	"	150	5	50	1 W	150	1	100	65~450	5	10	10	-10	V _{CEO} = 150mV (10V, 1mA, R _{CE} = 100kΩ, G _{CE} = 80dB)	160 *	2					165	2SA1124 とコンプリ	
" 2633	"	"	"	150	5	50	1.5W	150	1	100	65~450	5	10	10	-10		160 *	2					268	2SA1125 とコンプリ	
" 2634	"	"	"	60	7	100	400	150	0.1	10	180~700	5	2										138		
" 2635	日 立	SW	Si. T	650	6	100	750	150	I _{CEO} 5	V _{CE} 500	35~200	20	20	10	-10					15 *	<25			84B	2SA1126 とコンプリ
" 2636	松 下	Osc. Mix	Si. EP	30	3	50	400	125			>25	10	2						1200*					161	
" 2637	"	RF	Si. TP	300	7	100	1.4W	150			50~250	50	10	30	-20				100 *					151	
" 2638	東 芝	PA	Si. EP	35	3.5	2 A	15W (T _a =25℃)	175	100	15	>10	5	1 A			P _a > 6 W, η > 60% (f = 175MHz, V _{CE} = 12.5V, P _i = 0.5W)				<25			279		
" 2639	"	"	"	35	3.5	3.5A	35W (T _a =25℃)	175	1 mA	15	>10	5	1 A			P _a > 15 W, η > 60% (f = 175MHz, V _{CE} = 12.5V, P _i = 1.3 W)				<80			279		
" 2640	"	"	"	40	4	6 A	70W (T _a =25℃)	175	2 mA	15	>10	5	5 A			P _a > 28 W, η > 60% (f = 175MHz, V _{CE} = 12.5V, P _i = 4 W)				110			279		
" 2641	"	"	"	35	3.5	1.4A	15W (T _a =25℃)	175	1 mA	15	>10	5	1 A			P _a > 6 W, η > 60% (f = 470MHz, V _{CE} = 12.6V, P _i = 1 W)				15			279		
" 2642	"	"	"	35	3.5	2.8A	30W (T _a =25℃)	175	1.5mA	15	>10	5	1.5A			P _a > 12 W, η > 60% (f = 470MHz, V _{CE} = 12.6V, P _i = 3 W)				28			279		
" 2643	"	"	"	35	3.5	6 A	50W (T _a =25℃)	175	1 mA	15	>10	5	3 A			P _a > 25 W, η > 60% (f = 470MHz, V _{CE} = 12.6V, P _i = 8 W)				<80			279		
" 2644																									
" 2645	松 下	Osc. Mix	Si. EP	30	3	50	200	135			>25	10	2	-10		G _p = 20dB (f = 200MHz)				1200*			337C		
" 2646	"	RF.Mix.Osc.	"	30	3	50	200	125	0.1	10	120	10	2	10	-15				1200*	2		15	38B		
" 2647	"	RF	"	30	5	30	250	135			40~50	10	1	10	-1				230 *	1.3 *	Z _{in} < 60Ω		151		
" 2648	東 芝	PA	Si. E	35	3.5	3.5A	30W (T _a =25℃)	175	1 mA	15	50	5	1 A			P _a = 17 W (f = 470MHz, V _{CE} = 12.6V, P _i = 6 W)							316		
" 2649	"	"	"	35	3.5	6 A	50W (T _a =25℃)	175	1 mA	15	50	5	3 A			P _a = 22 W (f = 470MHz, V _{CE} = 12.6V, P _i = 6 W)							316		
" 2650																									
" 2651																									